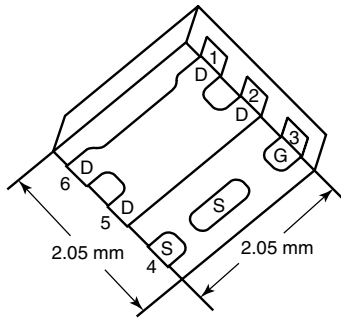


N-Channel 8-V (D-S) MOSFET

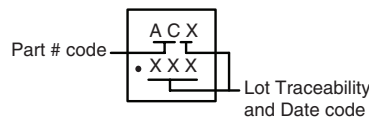
PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ)
8	0.011 at $V_{GS} = 4.5$ V	12	19 nC
	0.013 at $V_{GS} = 2.5$ V	12	
	0.016 at $V_{GS} = 1.8$ V	12	
	0.022 at $V_{GS} = 1.5$ V	12	
	0.041 at $V_{GS} = 1.2$ V	12	

PowerPAK SC-70-6L-Single



Marking Code



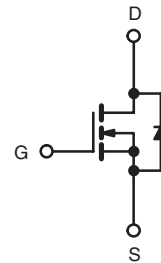
Ordering Information: SiA414DJ-T1-E3 (Lead (Pb)-free)

FEATURES

- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC70 Package
- Small Footprint Area

APPLICATIONS

- Load Switch for Portable Applications

RoHS
COMPLIANT

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	8	V
Gate-Source Voltage	V_{GS}	± 5	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	12 ^a	A
	$T_C = 70$ °C	12 ^a	
	$T_A = 25$ °C	12 ^{a, b, c}	
	$T_A = 70$ °C	11.6 ^{b, c}	
Pulsed Drain Current	I_{DM}	40	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	12 ^a	
	$T_A = 25$ °C	2.9 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	19	W
	$T_C = 70$ °C	12	
	$T_A = 25$ °C	3.5 ^{b, c}	
	$T_A = 70$ °C	2.2 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	28	36	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	5.3	6.5	

Notes:

a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5$ sec.d. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SC70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 80 °C/W.

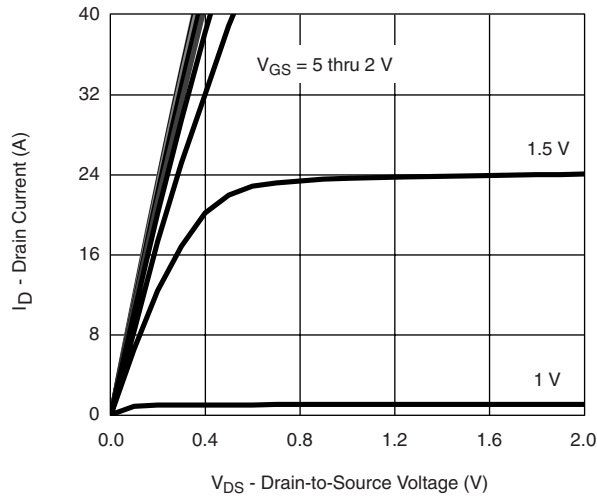
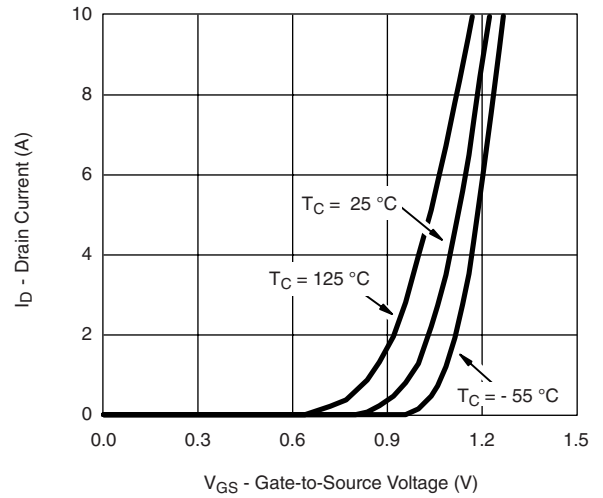
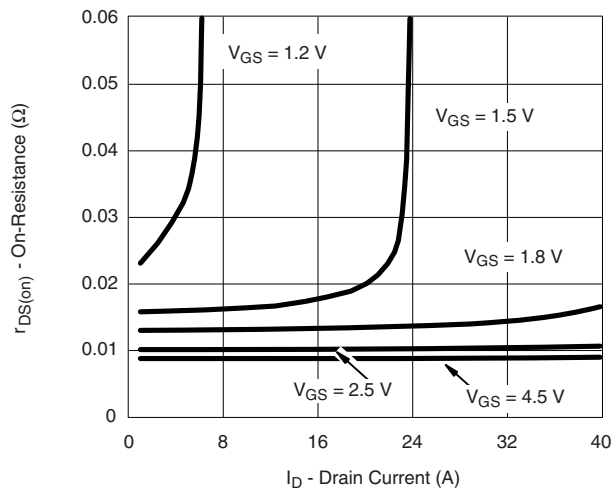
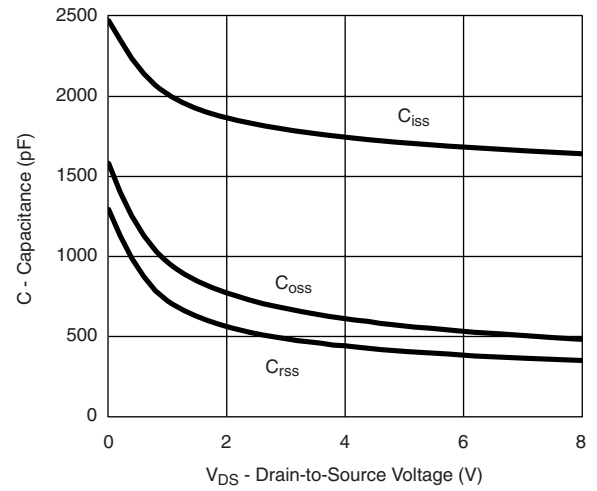
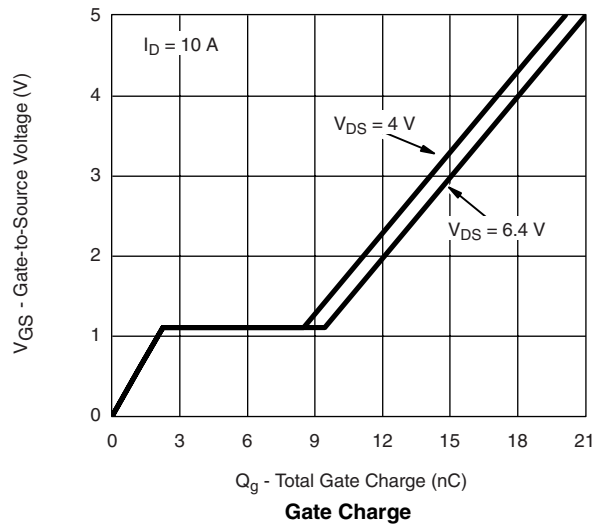
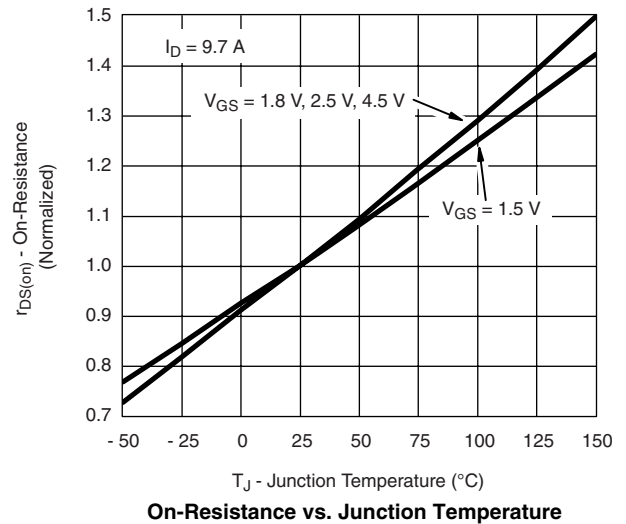
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		9		mV/ $^{\circ}\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.35		0.8	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 5\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 8\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 8\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 4.5\text{ V}$	20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}$, $I_D = 9.7\text{ A}$		0.009	0.011	Ω
		$V_{GS} = 2.5\text{ V}$, $I_D = 9\text{ A}$		0.011	0.013	
		$V_{GS} = 1.8\text{ V}$, $I_D = 8.1\text{ A}$		0.013	0.016	
		$V_{GS} = 1.5\text{ V}$, $I_D = 4.5\text{ A}$		0.016	0.022	
		$V_{GS} = 1.2\text{ V}$, $I_D = 2.4\text{ A}$		0.027	0.041	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 4\text{ V}$, $I_D = 9.7\text{ A}$		50		S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = 4\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1800		pF
Output Capacitance	C_{oss}			650		
Reverse Transfer Capacitance	C_{rss}			450		
Total Gate Charge	Q_g	$V_{DS} = 4\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 10\text{ A}$		21	32	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 4\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$		19	29	
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$		6.5		Ω
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 4\text{ V}$, $R_L = 0.4\text{ }\Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\text{ }\Omega$		2.5		ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			10	15	
Fall Time	t_f			65	100	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 4\text{ V}$, $R_L = 0.4\text{ }\Omega$ $I_D \cong 10\text{ A}$, $V_{GEN} = 5\text{ V}$, $R_g = 1\text{ }\Omega$		20	30	
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			10	15	
Fall Time	t_f			35	55	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			12	A
Pulse Diode Forward Current	I_{SM}				40	
Body Diode Voltage	V_{SD}	$I_S = 10\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$		40	80	ns
Body Diode Reverse Recovery Charge	Q_{rr}			20	40	nC
Reverse Recovery Fall Time	t_a			12		ns
Reverse Recovery Rise Time	t_b			28		

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

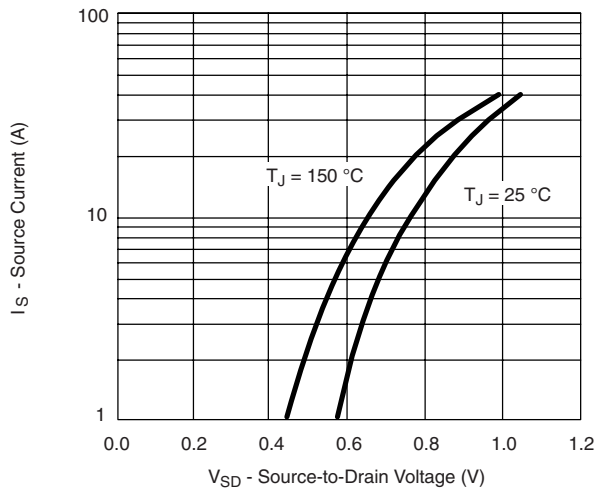
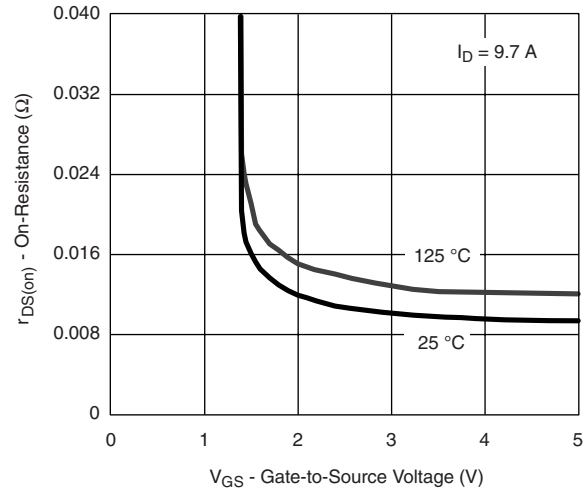
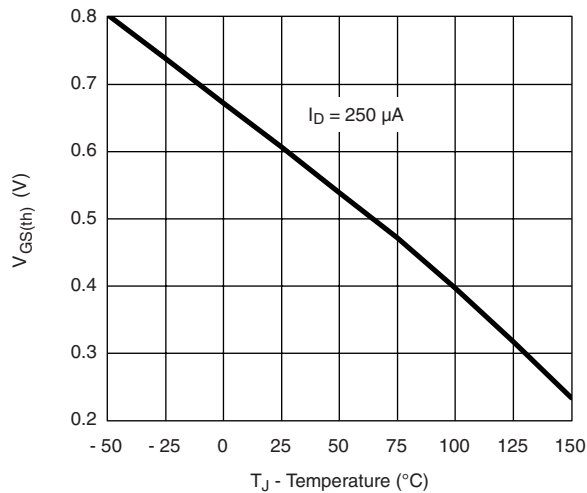
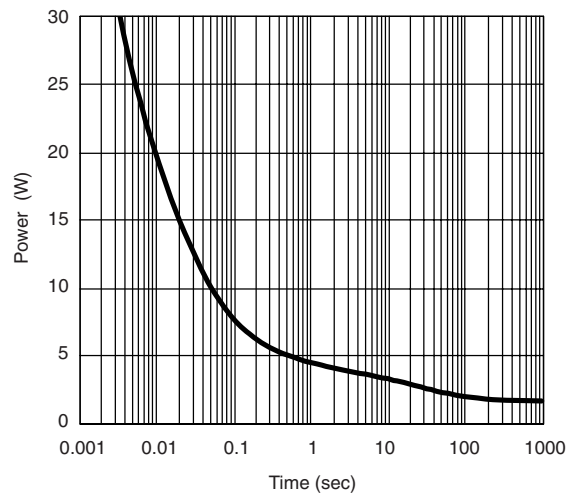
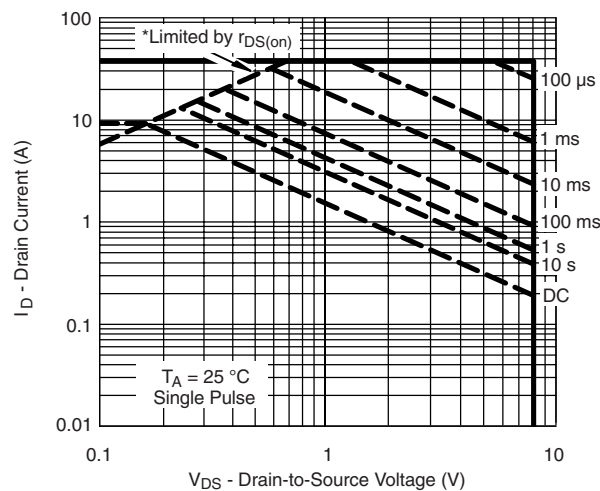
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

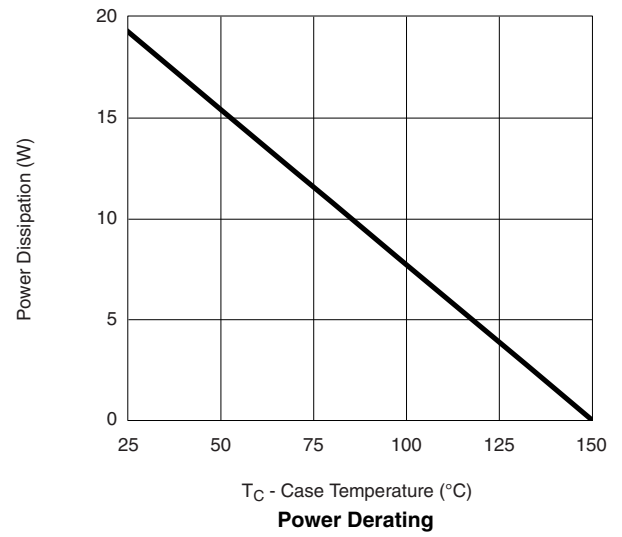
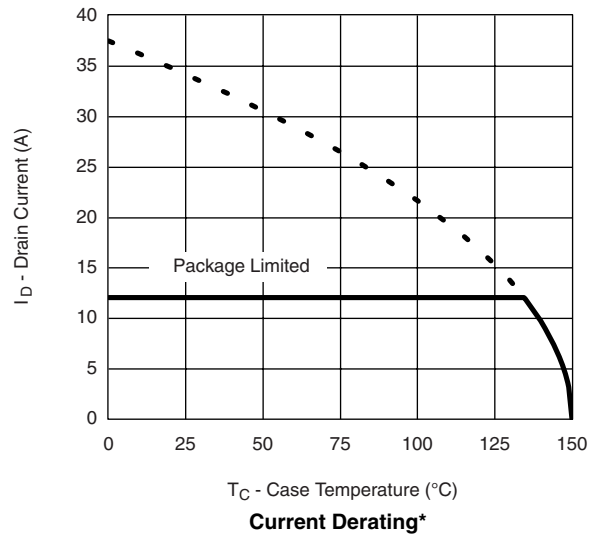
SiA414DJ

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power (Junction-to-Ambient)*** $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Ambient**



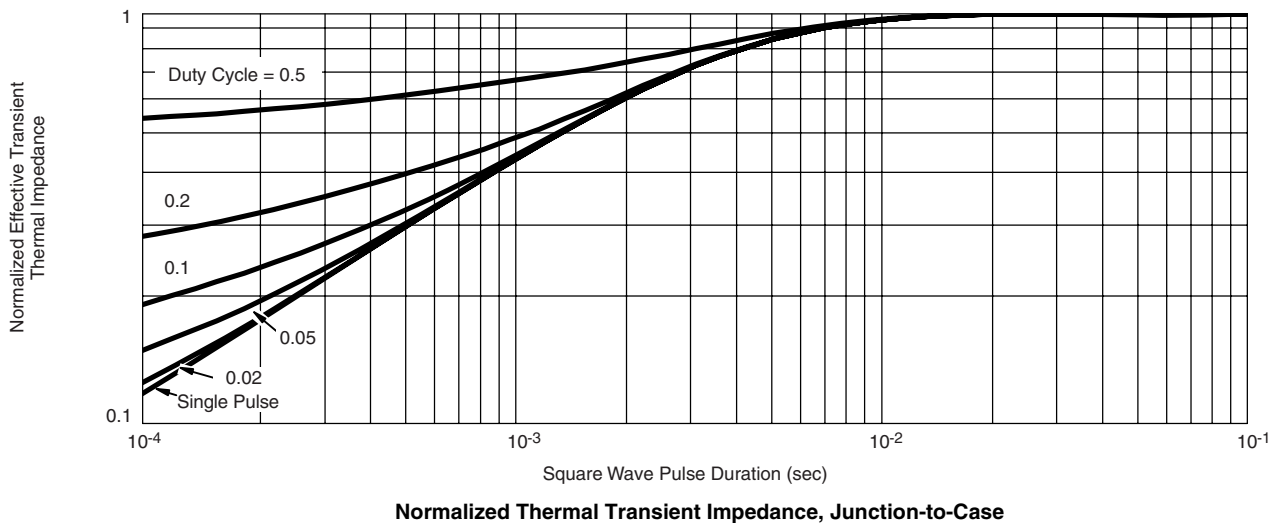
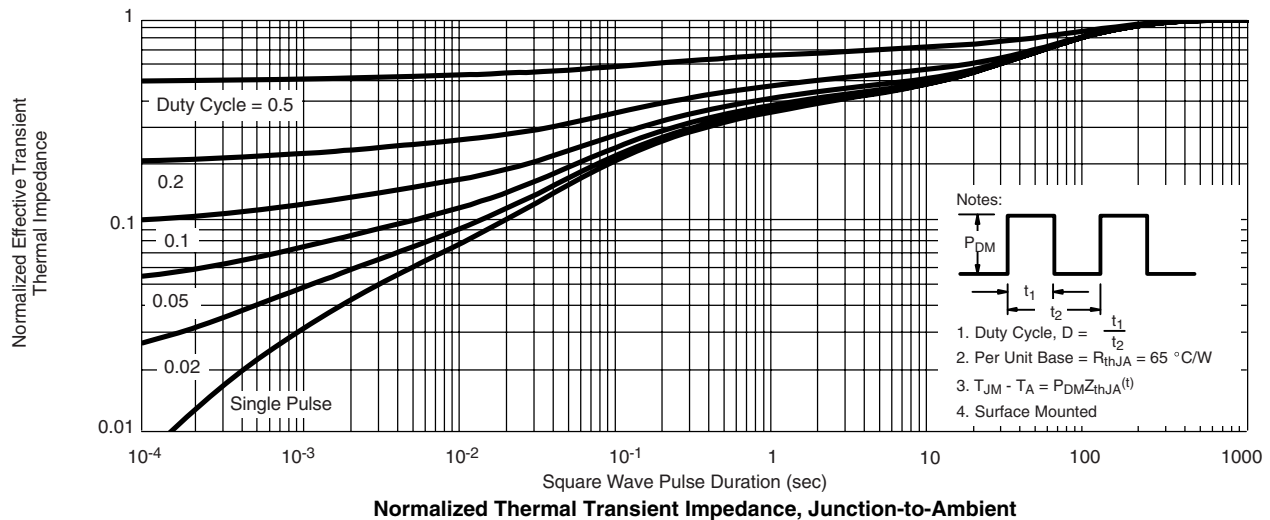
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiA414DJ

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73954>.



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